

## **isc Silicon NPN Power Transistor**

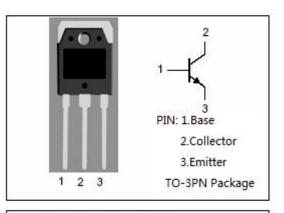
# BUV48B

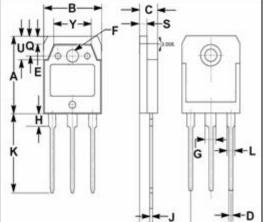
### DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub>= 600V (Min)
- High Current Capability
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• Designed for switching and industrial applications from single and three-phase mains.





	mm	
DIM	MIN	MAX
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
Κ	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

## Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>сво</sub>	Collector-Base Voltage	1200	V
V <sub>CEO</sub>	Collector-Emitter Voltage	600	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
lc	Collector Current-Continuous	15	А
I <sub>CM</sub>	Collector Current-Peak tp< 5ms	30	А
I <sub>B</sub>	Base Current-Continuous	4	А
I <sub>BM</sub>	Base Current-peak t <sub>p</sub> < 5ms	20	А
Pc	Collector Power Dissipation @Tc=25°C	125	W
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R <sub>th</sub> j-c	Thermal Resistance, Junction to Case	1.0	°C/W

isc website: www.iscsemi.com



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	600		V
V <sub>CER(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 0.5A; L= 2mH; V <sub>clamp</sub> = 1200V R <sub>BE</sub> = 10 Ω	1200		V
V <sub>CE(sat)</sub> -1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.5A		1.5	V
V <sub>CE (sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 4A		3.0	V
V <sub>BE</sub> (sat)-1	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.5A		1.5	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 4A		2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1200V ; I <sub>B</sub> = 0		0.5	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 600V; I <sub>B</sub> = 0		1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0		1.0	mA

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